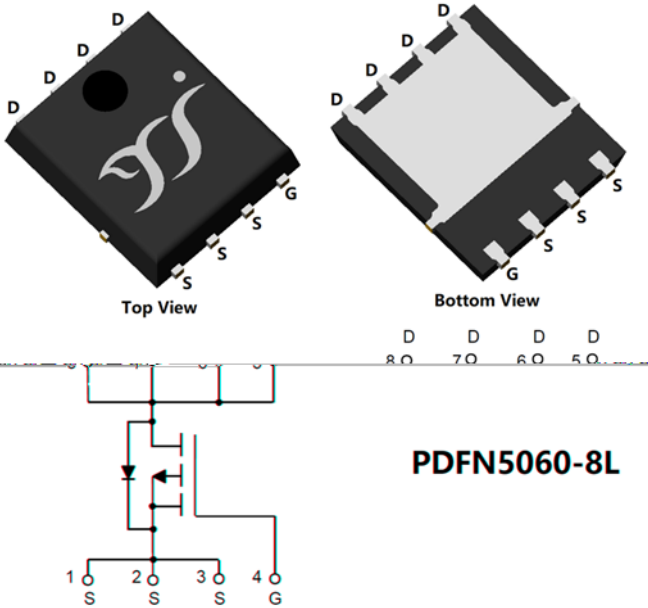


P-Channel Enhancement Mode Field Effect Transistor



Product Summary

V_{DS}	-60V
I_D	-40A
$R_{DS(ON)}$ (at $V_{GS}=-10V$)	<25 mohm
$R_{DS(ON)}$ (at $V_{GS}=-4.5V$)	<30 mohm
100% EAS Tested	
100% ∇V_{DS} Tested	

General Description

- Split gate trench MOSFET technology
- Low $R_{DS(on)}$ & FOM
- Low C_{rss}
- Extremely low switching loss
- Excellent stability and uniformity
- Moisture Sensitivity Level 1
- Epoxy Meets UL 94 V-0 Flammability Rating
- Halogen Free

Applications

- Load Switch
- Industrial DC/DC Conversion Circuits

Absolute Maximum Ratings ($T_A=25^\circ C$ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-source Voltage	V_{DS}	-60	V
Gate-source Voltage	V_{GS}	± 20	V
Drain Current	I_D	$T_c=25^\circ C$	-40
		$T_c=100^\circ C$	-25
Pulsed Drain Current ^A	I_{DM}	-160	A
Avalanche energy ^B	EAS	256	mJ
Total Power Dissipation ^C	P_D	$T_c=25^\circ C$	88
		$T_c=100^\circ C$	35.2
Junction and Storage Temperature Range	T_J, T_{STG}	-55~+150	$^\circ C$

Thermal resistance

Parameter	Symbol	Typ	Max	Units
Thermal Resistance Junction-to-Ambient ^D	R	15	20	$^\circ C/W$
Thermal Resistance Junction-to-Ambient ^D		Steady-State	40	
Thermal Resistance Junction-to-Case	R	1.15	1.42	

Ordering Information (Example)

PREFERRED P/N	PACKING CODE	Marking	MINIMUM PACKAGE(pcs)	INNER BOX QUANTITY(pcs)	OUTER CARTON QUANTITY(pcs)	DELIVERY MODE
YJG40GP06A	F1	YJG40GP06A	5000	10000	100000	13 reel



YJG40GP06A

Electrical Characteristics (T_J=25°C unless otherwise noted)

Parameter	Symbol	Conditions	Min	Typ	Max	Units
Static Parameter						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V, I _D =-250	-60			V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =-60V, V _{GS} =0V	T _J =25°C		-1	
			T _J =55°C		-5	
Gate-Body Leakage Current	I _{GSS}	V _{GS} = ±20V, V _{DS} =0V			±100	nA
Gate Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D =-250	-1.3	-1.8	-2.5	V
Static Drain-Source On-Resistance	R _{DS(on)}	V _{GS} = -10V, I _D =-20A		16	25	m
		V _{GS} = -4.5V, I _D =-10A		23	30	
Gate Resistance	R _g	f=1MHz		6		
Diode Forward Voltage	V _{SD}	I _S =-20A, V _{GS} =0V		-0.85	-1.3	V
Maximum Body-Diode Continuous Current	I _S				-40	A
Dynamic Parameters						
Input Capacitance	C _{iss}	V _{DS} =-30V, V _{GS} =0V, f=1MHz		2200		pF
Output Capacitance	C _{oss}			700		
Reverse Transfer Capacitance	C _{rss}			56		
Switching Parameters						
Total Gate Charge	Q _{g(-10V)}	V _{GS} =-10V, V _{DS} =-30V, I _D =-20A		37.5		nC
Total Gate Charge	Q _{g(-4.5V)}			17.4		
Gate-Source Charge	Q _{gs}			8.8		
Gate-Drain Charge	Q _{gd}			7.1		
Reverse Recovery Charge	Q _{rr}	I _F =-20A, di/dt=100A/us		22.3		
Reverse Recovery Time	t _{rr}			33.2		
Turn-on Delay Time	t _{D(on)}	V _{GS} =-10V, V _{DD} =-30V, R _L =2.5 R _{GEN} =6		9.9		ns
Turn-on Rise Time	t _r			39.2		
Turn-off Delay Time	t _{D(off)}			72.5		
Turn-off fall Time	t _f			64.7		

A. Repetitive rating; pulse width limited by max. junction temperature.

B. V_{DD}=50V, R_G 2mH, I_{AS}=16A.

C. Pd is based on max. junction temperature, using junction-case thermal resistance.

D. The value of R_{qJA} is measured with the device mounted on 1in2 FR-4 board with 2oz. Copper, in a still air environment with T_A =25°C. The Power d application depends on the user's specific board design.



Typical Performance Characteristics

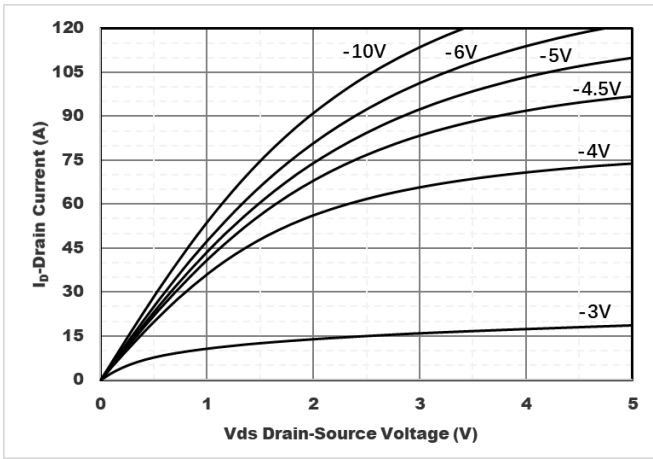


Figure1. Output Characteristics

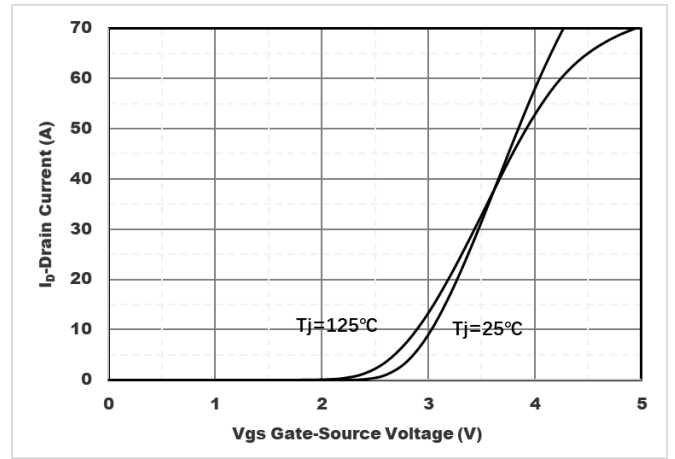


Figure2. Transfer Characteristics

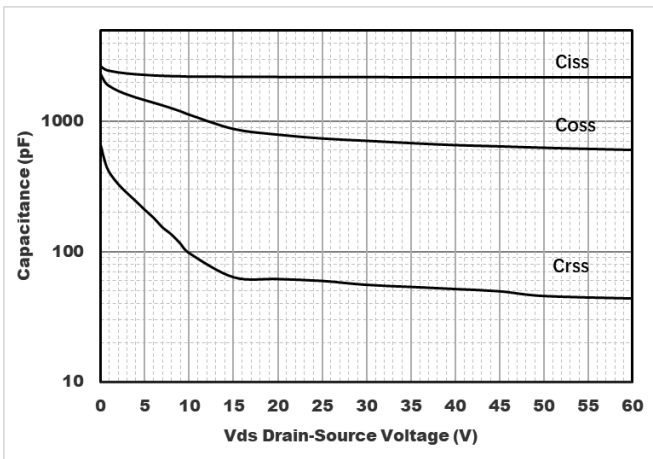


Figure3. Capacitance Characteristics

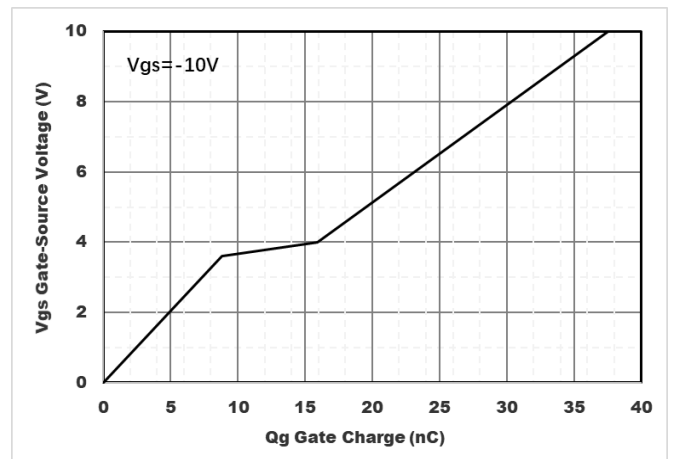


Figure4. Gate Charge

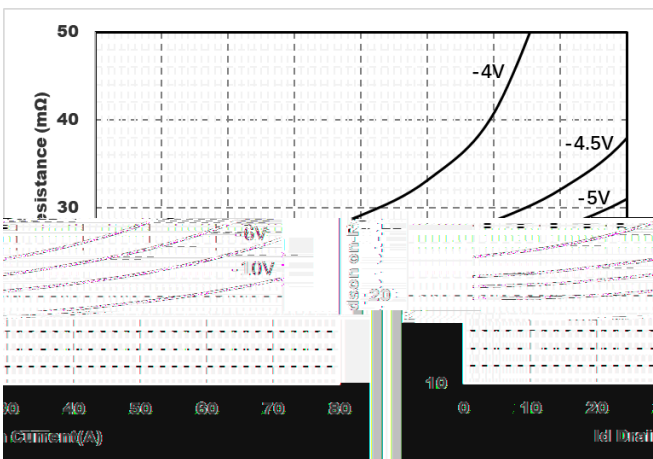


Figure5. : On-Resistance vs. Gate to Source Voltage

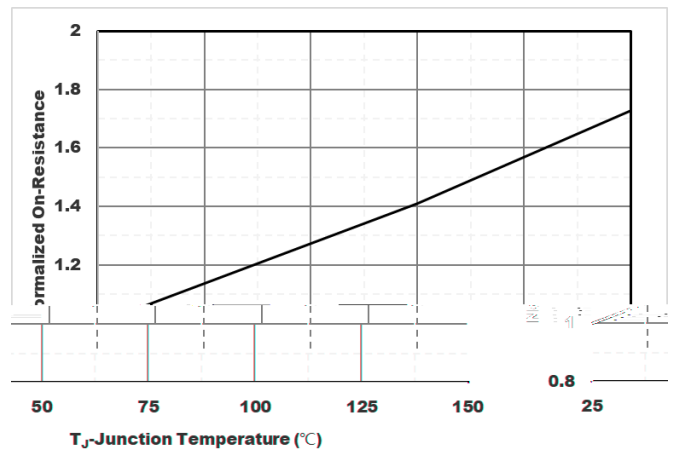


Figure6. Normalized On-Resistance



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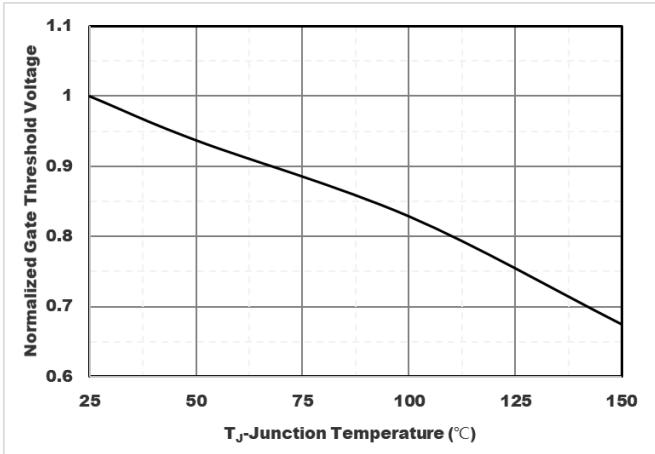


Figure7. Normalized Gate Threshold Voltage

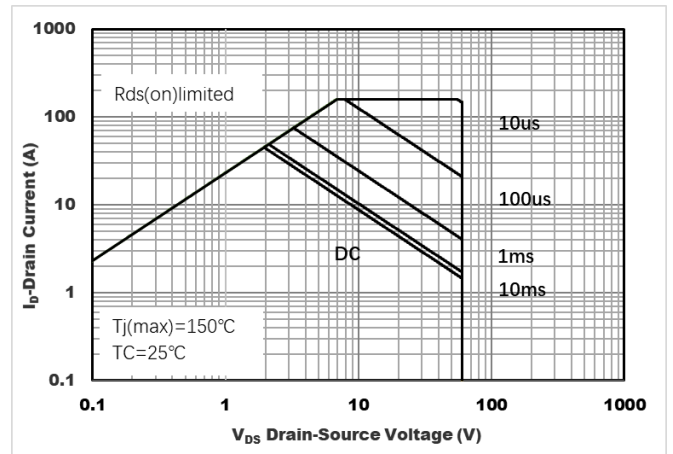


Figure8.Safe Operation Area

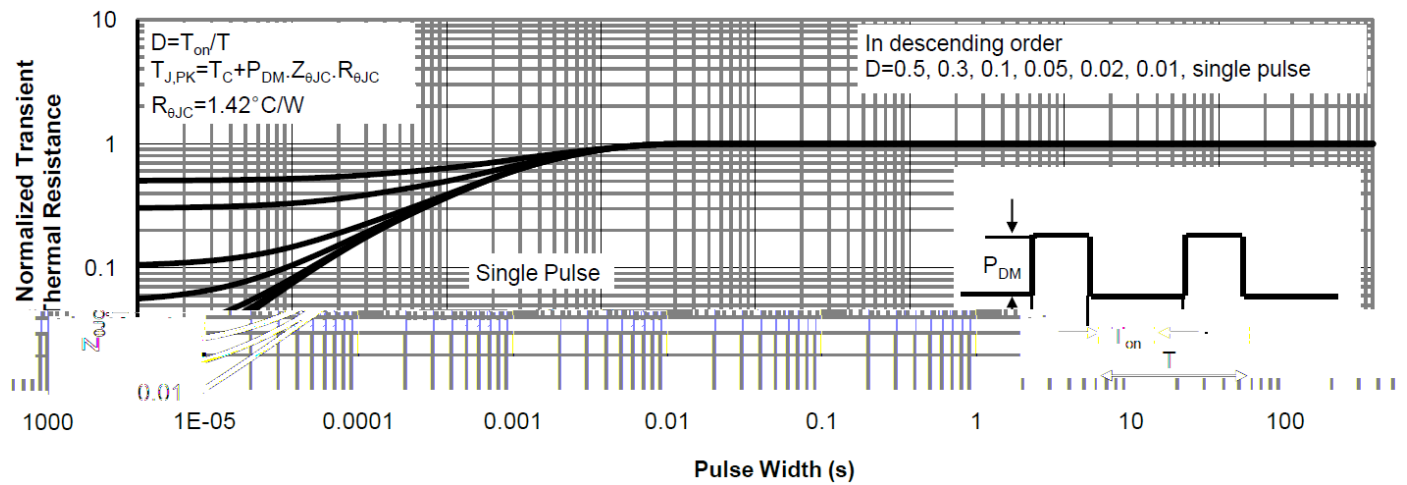
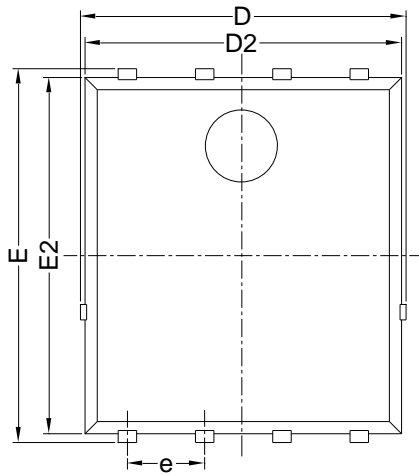


Figure9.Normalized Maximum Transient thermal impedance

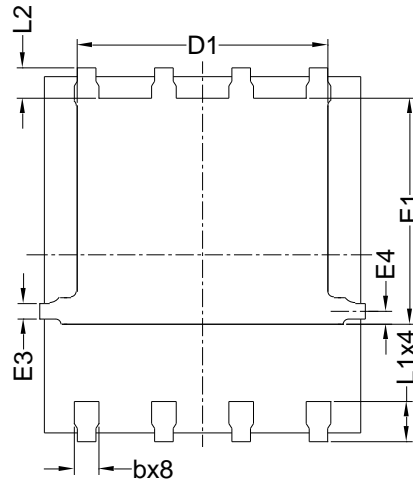


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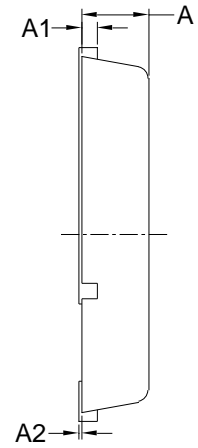
PDFN5060-8L-B-1.1MM Package information



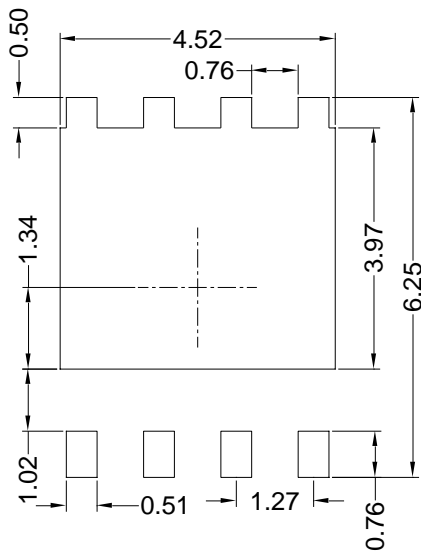
Top View
正面视图



Bottom View
背面视图



Side View
侧面视图



Suggested Solder Pad Layout
Top View

SYMBOL	MILLIMETER		
	MIN	NOM	MAX
D	5.15	5.35	5.55
E	5.95	6.15	6.35
A	1.00	1.10	1.20
A1	0.254 BSC		
A2			0.10
D1	3.92	4.12	4.32
E1	3.52	3.72	3.92
D2	5.00	5.20	5.40
E2	5.66	5.86	6.06
E3	0.254 REF		
E4	0.21 REF		
L1	0.56	0.66	0.76
L2	0.50 BSC		
b	0.31	0.41	0.51
e	1.27 BSC		

Note:

1. Controlling dimension: in millimeters.
2. General tolerance: ± 0.10 mm.
3. The pad layout is for reference purposes only.



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